Sheet: 1 of: 2

FORM:	PTO-1449
(REV:	7-80)

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

Atty Docket No: 92-0466.04

1/12/01

Serial No:

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant:
David A. Cathey

Filing Date:

Group:

(37 CFR 1.98(b))

(use several sheets if necessary)

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Initial		Number	Date	Name	Class	Subclass	60
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and	DD	Millman, J. et al., <u>Integrated Electronics</u> : Analog and Digital Circuits and System, pp. 204-205, 1972 (no month).

EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.

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Initial	Number	Date	Country	Class	Subclass	Yes	No

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	BB		
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